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S.Y. (Ron) Hui, *City University of Hong Kong*

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Integrated Low Power and High Bandwidth Optical Isolator for Monolithic Power MOSFETs Driver 356

Nicolas Rouger, Jean-Christophe Cr  bier, Olivier Lesaint, *Grenoble Electrical Engineering Lab / Grenoble University*

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Design and Characterization of a Signal Insulation Coreless Transformer Integrated in a CMOS Gate Driver Chip 360

Timoth   Simonot, Nicolas Rouger, Jean-Christophe Cr  bier, *Grenoble Electrical Engineering Lab / Grenoble University*; Jean-Daniel Arnould, *Grenoble Institute of Technology / IMEP-LAHC*

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Reduction of Conducted Electromagnetic Interference in SMPS Using Programmable Gate Driving Strength 364

A. Shorten, A.A. Fomani, W.T. Ng, *University of Toronto*; H. Nishio, Y. Takahashi, *Fuji Electric Co. Ltd.*

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Session 13 – Low Voltage Power Devices

Chairs: Jan Sonsky, *NXP*
Andy Strachan, *National Semiconductor*

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Self-Heating Analysis of Power MOSFET Module During Burn-in Test 368

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Gael Blondel, Blaise Rouleau, *VALEO VES*

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Hiroki Fujii, Shinichi Komatsu, Masaharu Sato, Toshihiko Ichikawa, *Renesas Electronics Corporation*

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150 V, 100 m  , SOI Power LDMOS with High Avalanche Current Capability for MHz Frequency Power Switching Applications 376

Patrick M. Shea, Z. John Shen, *University of Central Florida*

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P-Type Isolated GGNMOS with a Deep Current Path for ESD Protection 380

Jae-Hyun Yoo, Jongmin Kim, Joong-Hyeok Byeon, Young-Sang Son, Jaeyoung Park, Won-Young Jung, *Dongbu HiTek*